

Carbon-Quantum-Dot-Hybridized NiO_x Hole-Transport Layer Enables Efficient and Stable Planar p-i-n Perovskite Solar Cells with High Open-Circuit Voltage

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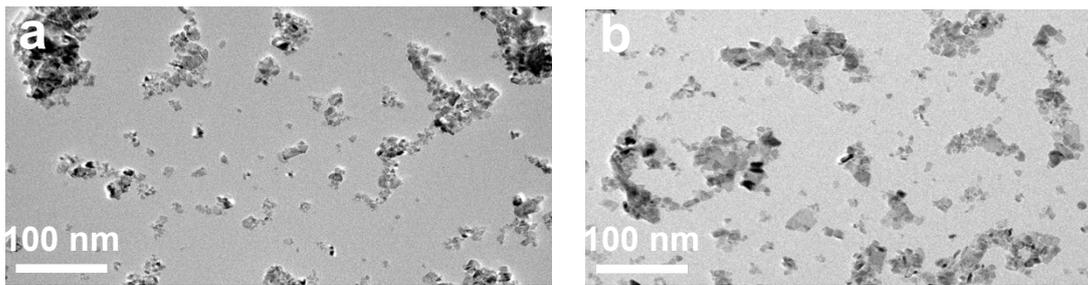


Figure S1. TEM images of a) the pristine NiO_x and b) CQDs-hybridized NiO_x dispersed in deionized water.

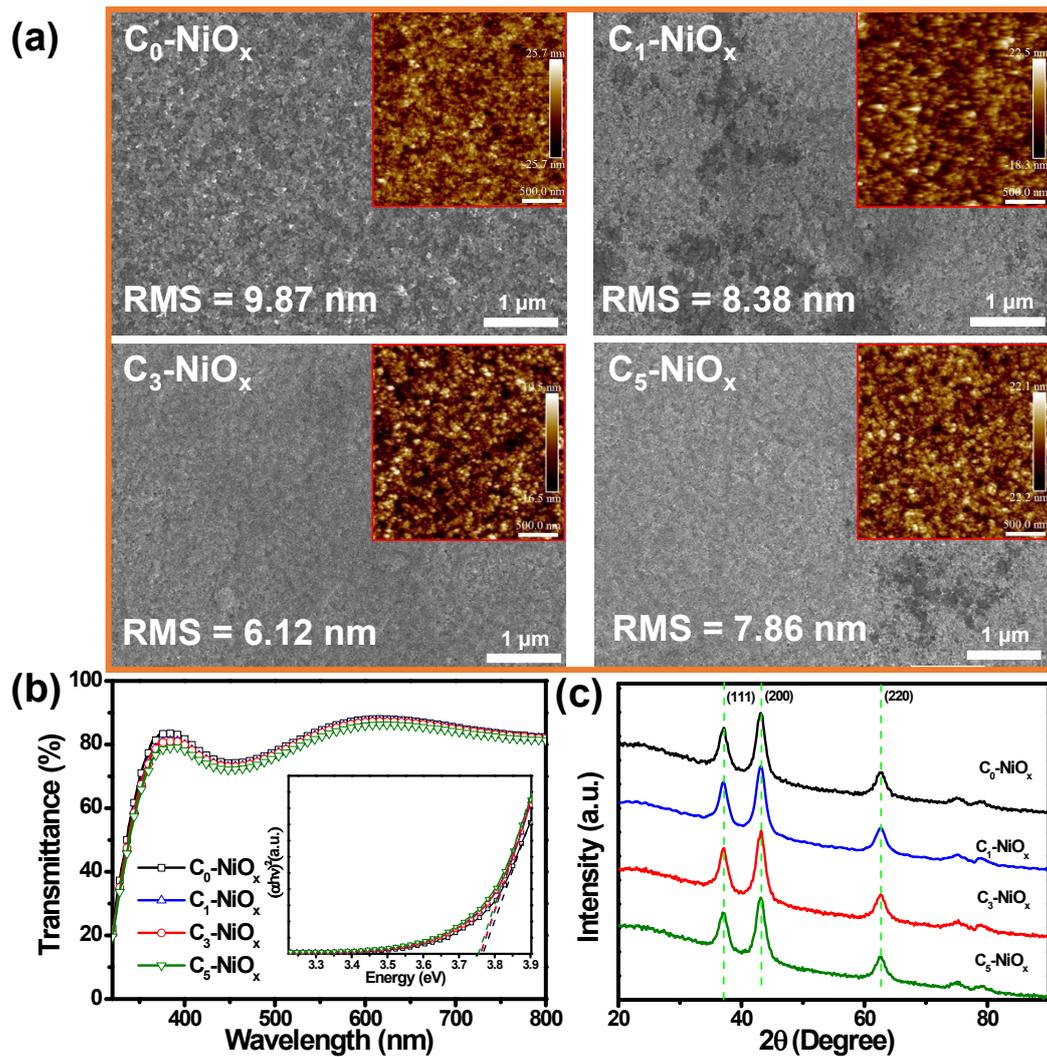


Figure S2. (a) FE-SEM and AFM (inset) images, (b) Optical transmittance (Inset: the corresponding Tauc plot of each film) and (c) X-ray diffraction spectra of the C_0 -NiO_x, C_1 -NiO_x, C_3 -NiO_x and C_5 -NiO_x films prepared on quartz substrates.

Table S1. Performance of the reported inverted planar MAPbI₃ PSCs based on NiO_x HTLs

| Device configuration | V_{oc} (V) | J_{sc} (mA cm ⁻²) | FF | PCE | Method | HTL | Ref |
|--|-----------------|---------------------------------------|------|-------|---------------|--------------------------|------|
| ITO/Cu:NiO _x /MAPbI ₃ /PC ₆₁ BM/bis-C ₆₀ /Ag | 1.11 | 19.01 | 0.73 | 15.40 | sol-gel | Cu:NiO _x | [1] |
| ITO/Cu:NiO _x /MAPbI ₃ /C ₆₀ /bis-C ₆₀ /Ag | 1.05 | 20.53 | 0.72 | 15.52 | combustion | Cu: NiO _x | [2] |
| ITO/Cu:NiO _x /MAPbI ₃ /C ₆₀ /BCP/Ag | 1.12 | 22.28 | 0.81 | 20.26 | NP ink | Cu: NiO _x | [3] |
| ITO/Cu:NiO _x /Cysteine/MAPbI ₃ /PCBM/Bphen/Al | 1.11 | 23.60 | 0.70 | 18.30 | combustion | Cu: NiO _x | [4] |
| FTO/Cu:NiO _x /MAPbI ₃ /PCBM /Ag | 1.06 | 20.79 | 0.67 | 14.88 | DCMS | Cu: NiO _x | [5] |
| ITO/Ag:NiO _x /MAPbI ₃ /PC ₇₁ BM/BCP /Ag | 1.08 | 19.70 | 0.80 | 16.86 | sol-gel | Ag: NiO _x | [6] |
| ITO/Co:NiO _x /MAPbI ₃ /PCBM/PEI/Ag | 1.05 | 22.30 | 0.79 | 18.60 | combustion | Co: NiO _x | [7] |
| FTO/Zn:NiO _x /MAPbI ₃ /PCBM/BCP/Ag | 1.10 | 22.80 | 0.78 | 19.6 | sol-gel | Zn: NiO _x | [8] |
| FTO/LiNiO/MAPbI ₃ -xCl _x /PCBM/Ag | 1.12 | 21.79 | 0.74 | 18.00 | magnetron | Li: NiO _x | [9] |
| FTO/NiMgO _x /MAPbI ₃ /PCBM/ZnMgO/Al | 1.08 | 21.30 | 0.80 | 18.50 | sol-gel | NiMgO | [10] |
| FTO/ Sr:NiO _x /MAPbI ₃ /PCBM/AgAl | 1.11 | 22.73 | 0.79 | 20.05 | sol-gel | Sr:NiO _x | [11] |
| TO/Cs:NiO _x /MAPbI ₃ /PCBM/ZrAcac/Ag | 1.12 | 21.77 | 0.79 | 19.35 | sol-gel | Cs: NiO _x | [12] |
| ITO/Li, Ag:NiO _x /MAPbI ₃ /PCBM/BCP/Ag | 1.13 | 21.29 | 0.80 | 19.24 | sol-gel | Li,Ag: NiO _x | [13] |
| FTO/La:NiO _x /MAPbI ₃ /PCBM/BCP/Ag | 1.01 | 21.02 | 0.73 | 15.46 | NP ink | La: NiO _x | [14] |
| ITO/Fe:NiO _x /MAPbI ₃ /PCBM/BCP/Ag | 1.08 | 19.10 | 0.84 | 17.40 | spray coating | Fe: NiO _x | [15] |
| FTO/NiO _x /MAPbI ₃ /PCBM/Ag | 1.03 | 17.42 | 0.71 | 12.70 | sol-gel | NiO _x | [16] |
| ITO/NiO _x (F4-TCNQ)/MAPbI ₃ /PCBM/BCP/Ag | 1.02 | 20.70 | 0.74 | 15.70 | sol-gel | F4-TCNQ:NiO _x | [17] |
| FTO/S:NiO _x /MAPbI ₃ /PCBM/PPDIN6/Ag | 1.10 | 23.28 | 0.80 | 20.43 | spray coating | S: NiO _x | [18] |
| FTO/NiO _x /MAPbI ₃ /PCBM/Ag | 1.01 | 18.30 | 0.81 | 14.95 | EBPVD | NiO _x | [19] |
| FTO NiO _x /MAPbI ₃ /C ₆₀ /SnO ₂ NCs/Ag | 1.12 | 21.8 | 0.77 | 18.80 | sol-gel | NiO _x | [20] |
| ITO/NiO/MAPbI ₃ /PCBM/PDINO/Ag | 1.11 | 20.57 | 0.76 | 17.50 | NP ink | NiO _x | [21] |

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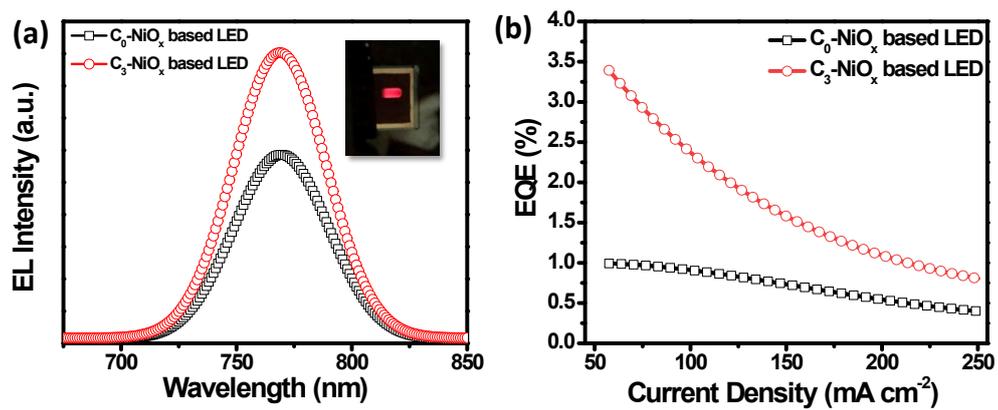


Figure S3. a) The electroluminescence spectra (EL) and b) EQE-current density curves for the best-performing C_0 -NiO_x and C_3 -NiO_x devices operating as LEDs (Insert: EL image of the C_3 -NiO_x device).

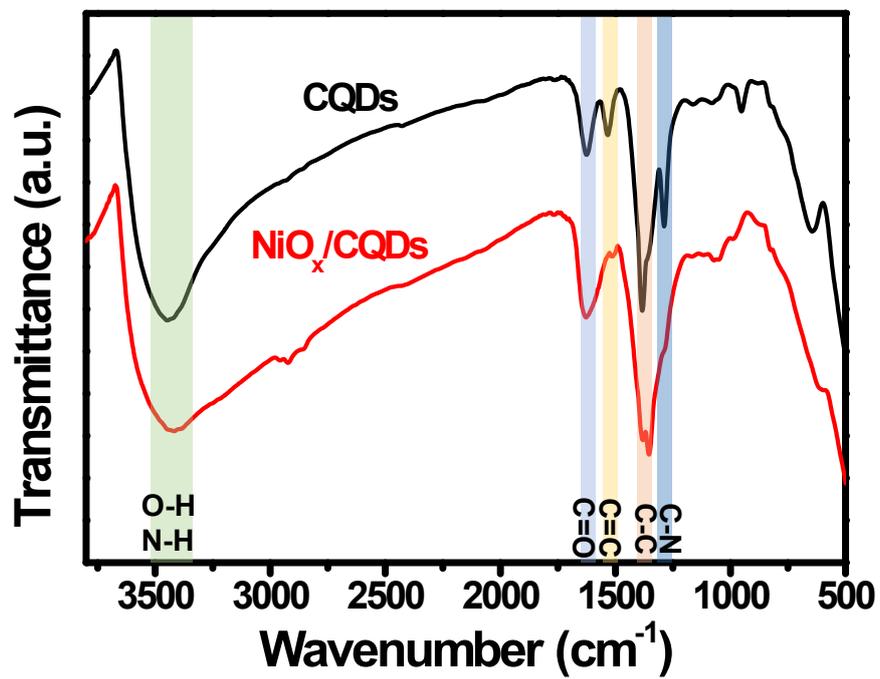


Figure S4. FT-IR spectra of the CQDs and CQDs-hybridized NiO_x films.

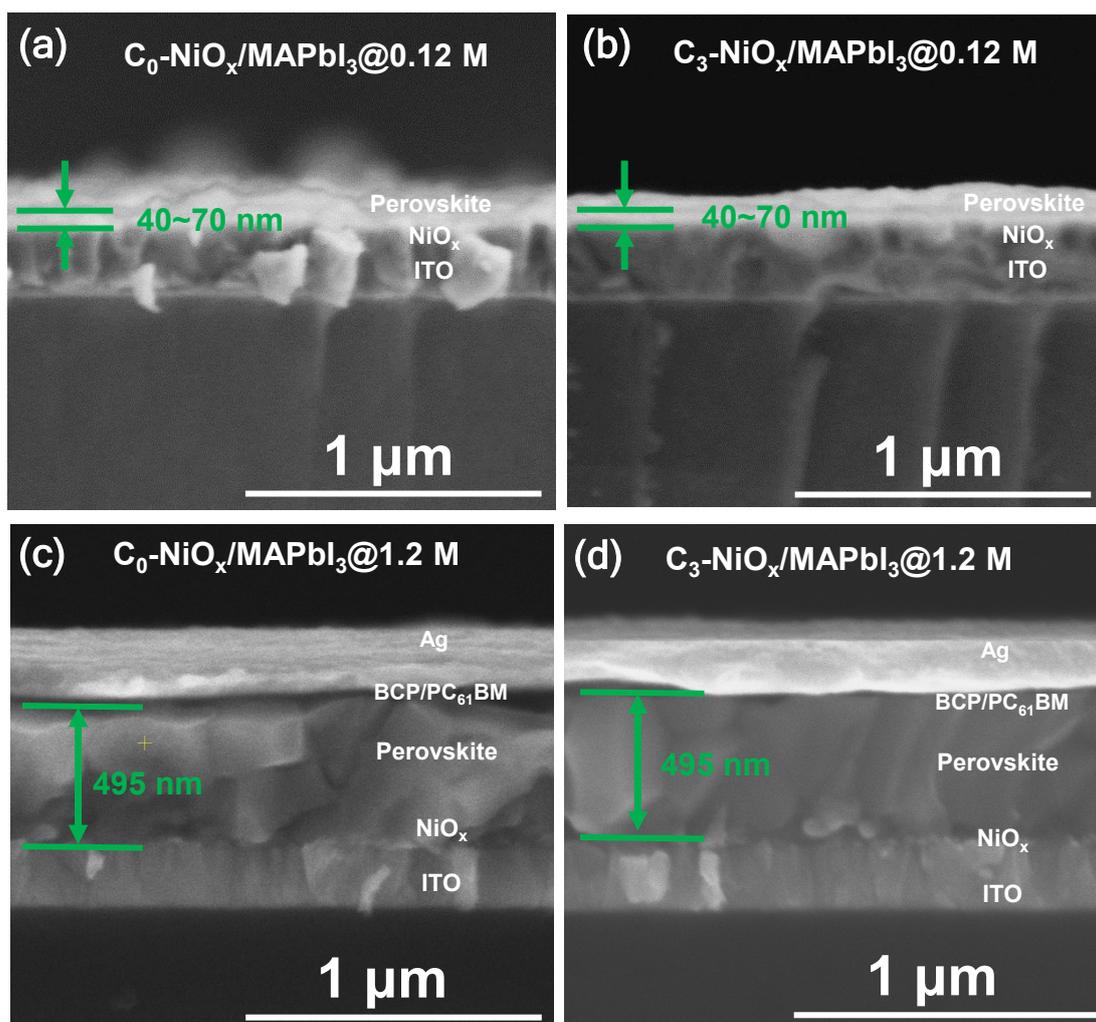


Figure S5. The cross-sectional SEM images of (a, b) thin perovskite films (casting from 0.12 M perovskite precursor solution) on $C_0\text{-NiO}_x$ and $C_3\text{-NiO}_x$ films, respectively, and (c, d) thick perovskite films (casting from 1.2 M perovskite precursor solution) on $C_0\text{-NiO}_x$ and $C_3\text{-NiO}_x$ films, respectively.

Table S2. XRD parameters of thin and thick perovskite films on C₀-NiO_x and C₃-NiO_x HTLs

| Concentrations | Samples | FWHM of (110) (degree) | Intensity ratio of (110) to (310) |
|----------------|----------------------------------|---------------------------|--------------------------------------|
| 0.12 M | C ₀ -NiO _x | 0.38 | 1.73 |
| | C ₃ -NiO _x | 0.27 | 8.31 |
| 1.20 M | C ₀ -NiO _x | 0.17 | 3.78 |
| | C ₃ -NiO _x | 0.12 | 4.76 |

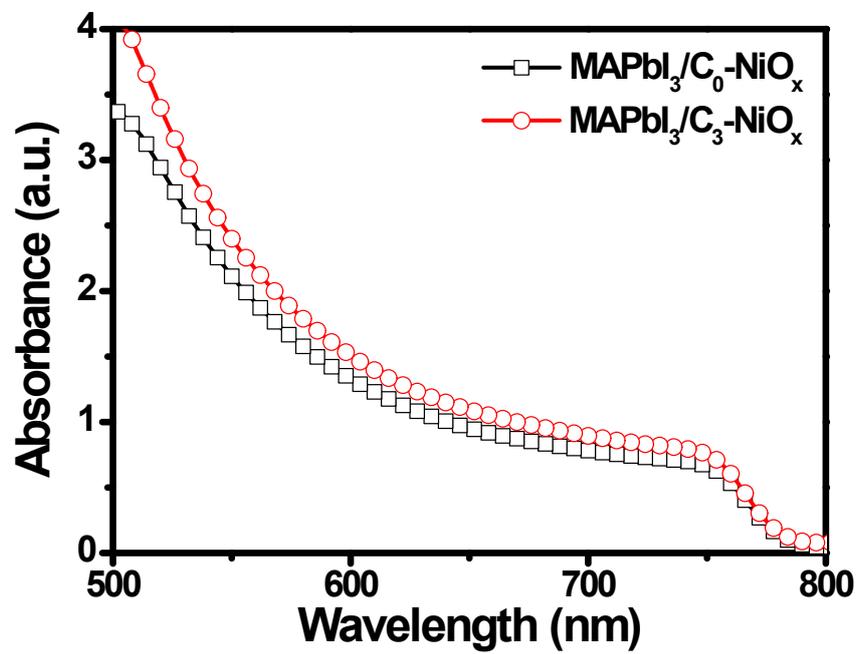


Figure S6. UV-vis absorption spectra of thick MAPbI₃ films deposited on the C₀-NiO_x and C₃-NiO_x films.

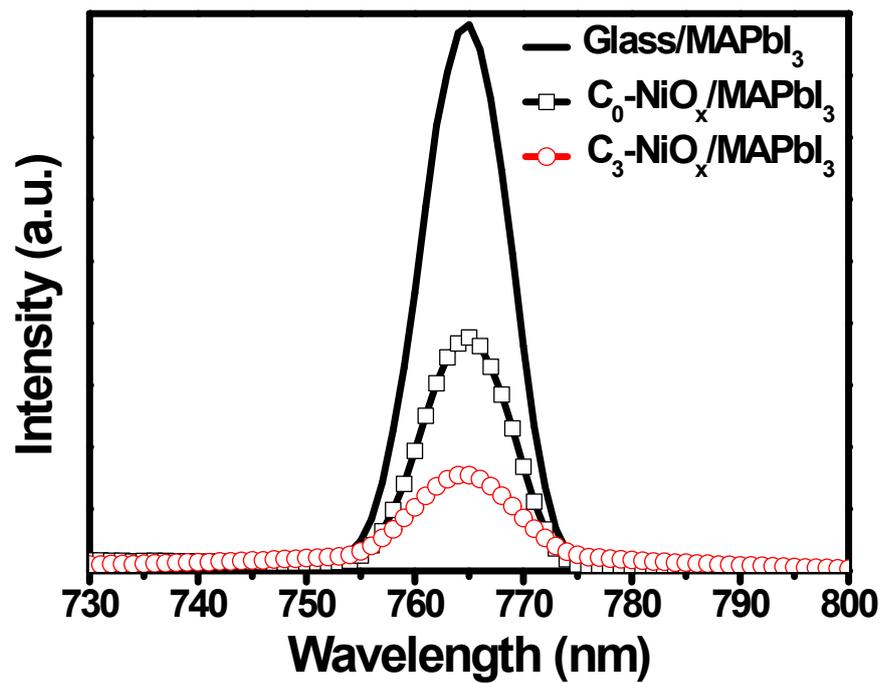


Figure S7. Steady-state PL spectra of MAPbI₃ perovskite films deposited on the glass, C₀-NiO_x and C₃-NiO_x films.